



东莞市华远电子有限公司

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TO-92L Plastic-Encapsulate Transistors

2SB562 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 900 mW ($T_{amb}=25$)

Collector current

I_{CM} : -1 A

Collector-base voltage

$V_{(BR)CBO}$: -25 V

Operating and storage junction temperature range

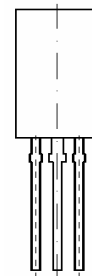
T_J , T_{stg} : -55 to +150

TO-92L

1. EMITTER

2. COLLECTOR

3. BASE



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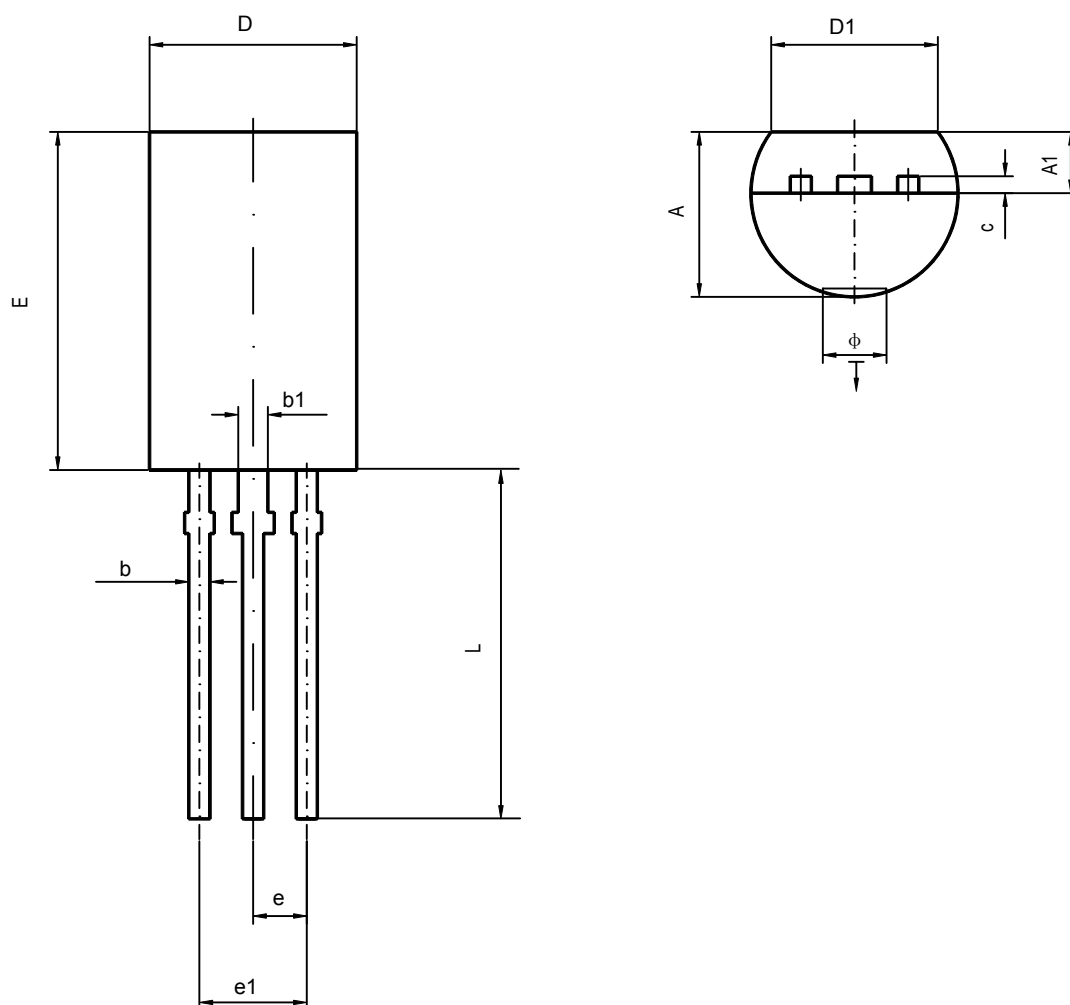
ELECTRICAL CHARACTERISTICS ($T_{amb}=25$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-20V, I_E=0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0$			-1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-2V, I_C=-0.5A$	85		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-0.8A, I_B=-0.08A$			-0.5	V
Base-emitter voltage	V_{BE}	$V_{CE}=-2V, I_C=-0.5A$			-1	V
Transition frequency	f_T	$V_{CE}=-2V, I_C=-0.5A$		350		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		38		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	B	C
Range	85-170	120-240

TO-92L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.700	4.100	0.146	0.161
A1	1.280	1.580	0.050	0.062
b	0.350	0.550	0.014	0.022
b1	0.600	0.800	0.024	0.031
c	0.350	0.450	0.014	0.018
D	4.700	5.100	0.185	0.201
D1	4.000		0.157	
E	7.800	8.200	0.307	0.323
e	1.270TYP		0.050TYP	
e1	2.440	2.640	0.096	0.104
L	13.800	14.200	0.543	0.559
ϕ		1.600		0.063
\downarrow	0.000	0.300	0.000	0.012